



Attorney Docket No. 5000.113B
Confirmation No. 7918

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re: David B. Slater, Jr.
Serial No. 10/799,140
Filed: 03/12/2004
For: LOW TEMPERATURE FORMATION OF
BACKSIDE OHMIC CONTACTS FOR
VERTICAL DEVICES

Group Art Unit 2825
Examiner L. H. Malsawma

January 5, 2005

MS Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT
CITATION UNDER 37 C.F.R. § 1.97

Sir:

Attached is an Information Disclosure Statement (IDS) by Applicants listing references that were cited in related patent applications. Copies of citation nos. 15, 16, 17, and 18 (i.e., the four of six cited non-patent documents) are enclosed. Copies of the remaining cited documents are not enclosed as these were provided in the corresponding parent application Ser. No. 09/787,189 filed March 15, 2001.

It is requested that the Examiner consider these documents and officially make them of record in accordance with the provisions of 37 C.F.R. § 1.97 and MPEP § 609.

Applicants are filing this IDS after the mailing of a first Office action, but before the issue of a final action or notice of allowance. Accordingly, a credit card payment form for the amount of \$180 is enclosed (37 C.F.R. 1.17(p)). The Commissioner is authorized to charge any additional fees that may be required, or credit any overpayment, to Deposit Account No. 50-0332.

Respectfully submitted,

R. Brian Johnson
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¹ Unique citation designation number. ² See attached Kinds of U.S. Patent Documents. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

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PTO/SB/08A (08-00)

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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Complete if Known	
		Application Number	10/799,140
		Filing Date	03/12/2004
		First Named Inventor	Slater
		Group Art Unit	2825
		Examiner Name	L. H. Malsawma
Sheet 2 of 2	Attorney Docket Number	5000.113B	

OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS			
Examiner Initials *	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
	15	SPIEL (aka "Spiess"), Aluminum implantation of p-SiC for ohmic contacts, First European Conference on Silicon Carbide and Related Materials (ECSCRM 96), Oct. 6-9, 1996, pp. 1414-1419, Vol. 6, no. 10, Elsevier, Switzerland	
	16	DEV ALOK et al, Low Contact Resistivity Ohmic Contacts to 6H-Silicon Carbide, Proceedings of the International Electron Devices Meeting, 1993, pp. 691-694, IEEE, New York	
	17	CHEN et al., Contact Resistivity of Re, Pt and Ta Films on n-Type Beta-SiC: Preliminary Results, Materials Science and Engineering, 01/01/1995, pp. 185-189, Vol. B29, no. 1/03, Elsevier Sequoia, Lausanne	
	18	PORTER et al, A critical review of ohmic and rectifying contacts for silicon carbide, Materials Science and Engineering, 11-01-1995, pp. 83-105, Vol. B34, no. 2/03, Elsevier Sequoia, Lausanne	
	19	A. MOKI et al.; Low Resistivity As-Deposited Ohmic Contacts to 3C-SiC; Journal of Electronic Materials; 1995; pp. 315-318; Vol. 24, No. 4	
	20	T. TADAO et al.; Lowering the Annealing Temperature of Ni/SiC for Ohmic Contacts under N(2) Gas, and Application to a UV Sensor; Materials Science Forum; pp. 989-992; Vols. 338-342 (2000)	

Examiner Signature		Date Considered	
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¹ EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Unique citation designation number. ² Applicant is to place a check mark here if English language Translation is attached.

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